

Supplementary: First principles investigation of electron mobility enhancement of β -Ga₂O₃ doped with Indium

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Table S1 the detailed TDOS of Ga₂O₃ and In-Ga₂O₃ near the CBM

Ga ₂ O ₃		In-Ga ₂ O ₃	
Energy(eV)	TDOS(1/eV)	Energy(eV)	TDOS(1/eV)
1.7874	0	1.7479	0
1.8564	0	1.8169	0
1.9254	0	1.8849	0
1.9954	0.00000096	1.9539	0.0005415
2.0644	0.01676	2.0219	0.009534
2.1334	0.06654	2.0909	0.02959
2.2034	0.1449	2.1589	0.06071
2.2724	0.1986	2.2279	0.1029
2.3424	0.2232	2.2959	0.1561
2.4114	0.2561	2.3649	0.2226
2.4804	0.2997	2.4329	0.3246
2.5504	0.3488	2.5019	0.4201
2.6194	0.4043	2.5709	0.4963
2.6894	0.494	2.6389	0.549

2.7584	0.5401	2.7079	0.5776
2.8274	0.5584	2.7759	0.586
2.8974	0.568	2.8449	0.5851

The matrix of elastic constants Cij (GPa) of pure Ga₂O₃ (in GPa)

[288.4, 140.2, 171.7, 0, 0, -20.6]

[140.2, 412.6, 123.4, 0, 0, 7.6]

[171.7, 123.4, 401.7, 0, 0, 6.5]

[0, 0, 0, 108.5, 20.4, 0]

[0, 0, 0, 20.4, 82.4, 0]

[-20.6, 7.6, 6.5, 0, 0, 83.2]

The matrix of elastic constants Cij (GPa) of In-Ga₂O₃ (in GPa)

[281.8, 130.1, 164.2, 0, 0, -20.2]

[139.1, 403.9, 122.3, 0, 0, 4.7]

[164.2, 122.3, 385.2, 0, 0, 1.7]

[0, 0, 0, 103.1, 18.0, 0]

[0, 0, 0, 18.0, 81.0, 0]

[-20.2, 4.7, 1.7, 0, 0, 75.4]

The matrix of elastic constants Cij (GPa) of Al-Ga₂O₃ (in GPa)

[295.8, 143.2, 170.1, 0, 0, -20.3]

[143.2, 419.0, 123.0, 0, 0, 8.1]

[170.1, 123.0, 406.5, 0, 0, 7.3]

[0, 0, 0, 110.7, 19.8, 0]

[0, 0, 0, 19.8, 83.6, 0]

[-20.3, 8.1, 7.3, 0, 0, 84.9]

The matrix of deformation potential of Ga₂O₃ (in eV)

$[[3.15 \quad 0.19 \quad 0.12]$
 $[0.19 \quad 2.16 \quad 0.01]$
 $[0.12 \quad 0.01 \quad 3.27]]$

The matrix of deformation potential of In-Ga₂O₃ (in eV)

$[[2.88 \quad 0.20 \quad 0.12]$
 $[0.20 \quad 2.17 \quad 0.02]$
 $[0.12 \quad 0.02 \quad 2.93]]$

The matrix of deformation potential of Al-Ga₂O₃ (in eV)

$[[3.29 \quad 0.21 \quad 0.17]$
 $[0.21 \quad 2.36 \quad 0.00]$
 $[0.17 \quad 0.00 \quad 3.30]]$

Table S2. Calculated Frohlich Parameter (α) and Schultz Polaron Radius (r_f) for Electrons in Ga₂O₃, Al-Ga₂O₃, In-Ga₂O₃ at T=300K

	α			r_f (Å)		
	Ga ₂ O ₃	Al-Ga ₂ O ₃	In-Ga ₂ O ₃	Ga ₂ O ₃	Al-Ga ₂ O ₃	In-Ga ₂ O ₃
average	1.16	1.25	1.17	145.8	138.1	142.3
x	1.12	1.23	1.14	148.9	139.0	144.2
y	1.07	1.15	1.05	154.0	144.0	149.7
z	1.25	1.32	1.26	141.1	133.9	136.8